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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	27
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-UFQFPN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l031k6u6tr

Contents STM32L031x4/6

		6.3.16 Temperature sensor characteristics	87
		6.3.17 Comparators	88
		6.3.18 Timer characteristics	
		6.3.19 Communications interfaces	
		0.5.19 Communications interfaces	90
7	Pack	age information	96
	7.1	LQFP48 package information	96
	7.2	LQFP32 package information	99
	7.3	UFQFPN32 package information	102
	7.4	UFQFPN28 package information	104
	7.5	WLCSP25 package information	106
	7.6	TSSOP20 package information	109
	7.7	Thermal characteristics	112
		7.7.1 Reference document	113
8	Part	numbering	114
9	Revi	sion history	115

List of tables STM32L031x4/6

Table 45.	RAM and hardware registers
Table 46.	Flash memory and data EEPROM characteristics
Table 47.	Flash memory and data EEPROM endurance and retention
Table 48.	EMS characteristics
Table 49.	EMI characteristics
Table 50.	ESD absolute maximum ratings
Table 51.	Electrical sensitivities
Table 52.	I/O current injection susceptibility
Table 53.	I/O static characteristics
Table 54.	Output voltage characteristics
Table 55.	I/O AC characteristics
Table 56.	NRST pin characteristics
Table 57.	ADC characteristics
Table 58.	R _{AIN} max for f _{ADC} = 16 MHz
Table 59.	ADC accuracy
Table 60.	Temperature sensor calibration values87
Table 61.	Temperature sensor characteristics
Table 62.	Comparator 1 characteristics
Table 63.	Comparator 2 characteristics
Table 64.	TIMx characteristics
Table 65.	I2C analog filter characteristics90
Table 66.	USART/LPUART characteristics
Table 67.	SPI characteristics in voltage Range 192
Table 68.	SPI characteristics in voltage Range 293
Table 69.	SPI characteristics in voltage Range 394
Table 70.	LQFP48 - 48-pin low-profile quad flat package, 7 x 7 mm, package mechanical data97
Table 71.	LQFP32, 7 x 7 mm, 32-pin low-profile quad flat package mechanical data 100
Table 72.	UFQFPN32, 5 x 5 mm, 32-pin package mechanical data
Table 73.	UFQPN28, 4 x 4 mm, 28-pin package mechanical data104
Table 74.	WLCSP25 - 2.097 x 2.493 mm, 0.400 mm pitch wafer level chip scale mechanical data 106
Table 75.	WLCSP25 recommended PCB design rules
Table 76.	TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch,
	package mechanical data
Table 77.	Thermal characteristics112
Table 78.	STM32L031x4/6 ordering information scheme114
Table 79.	Document revision history



Functional overview STM32L031x4/6

3.14.4 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 37 kHz internal RC and, as it operates independently of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

3.14.5 Window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.15 Communication interfaces

3.15.1 I²C bus

One I²C interface (I2C1) can operate in multimaster or slave modes. The I²C interface can support Standard mode (Sm, up to 100 kbit/s), Fast mode (Fm, up to 400 kbit/s) and Fast Mode Plus (Fm+, up to 1 Mbit/s) with 20 mA output drive on some I/Os.

The I²C interface supports 7-bit and 10-bit addressing modes, multiple 7-bit slave addresses (2 addresses, 1 with configurable mask). They also include programmable analog and digital noise filters.

	Analog filter	Digital filter		
Pulse width of suppressed spikes	≥ 50 ns	Programmable length from 1 to 15 I2C peripheral clocks		
Benefits	Available in Stop mode	Extra filtering capability vs. standard requirements. Stable length		
Drawbacks	Variations depending on temperature, voltage, process	Wakeup from Stop on address match is not available when digital filter is enabled.		

Table 10. Comparison of I2C analog and digital filters

In addition, I2C1 provides hardware support for SMBus 2.0 and PMBus 1.1: ARP capability, Host notify protocol, hardware CRC (PEC) generation/verification, timeouts verifications and ALERT protocol management. I2C1 also has a clock domain independent from the CPU clock, allowing the I2C1 to wake up the MCU from Stop mode on address match.

The I2C interface can be served by the DMA controller.

Refer to *Table 11* for the supported modes and features of I2C interface.

Pin descriptions STM32L031x4/6

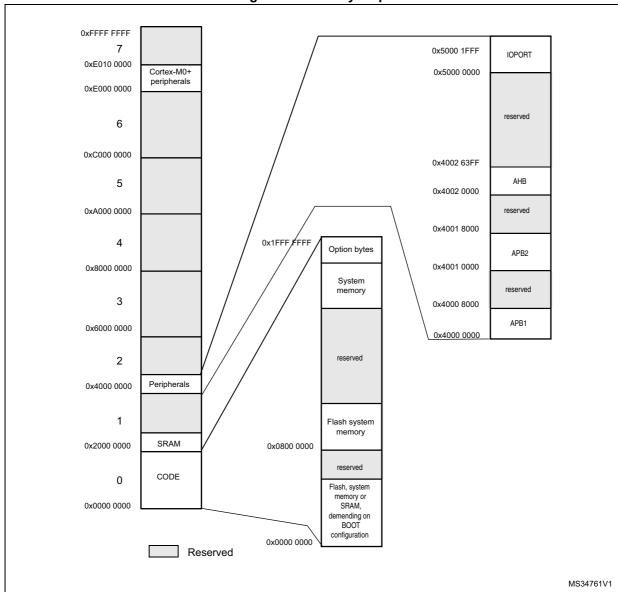
Table 15. Pin definitions (continued)

		Pin	Num	ber			Table 15. Pili							
TSSOP20	WLCSP25 ⁽¹⁾	UFQFPN28	UFQFPN28 (STM32L031GxUxS only)	LQFP32	UFQFPN32 ⁽²⁾	LQFP48	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions		
-	-	-	-	-	-	35	VSS	S	-	-	-	-		
-	D1	ı	-	-	-	36	VDD S		-	-				
20	A2	22	22	24	24	37	PA14	I/O	FT	-	SWCLK, LPTIM1_OUT, I2C1_SMBA, USART2_TX, LPUART1_TX	-		
-	-	23	23	25	25	38	PA15	I/O	FT	-	SPI1_NSS, TIM2_ETR, EVENTOUT, USART2_RX, TIM2_CH1			
-	B2	24	24	26	26	39	PB3	I/O	FT	-	SPI1_SCK, TIM2_CH2, EVENTOUT	COMP2_INN		
-	-	-	25	27	27	40	PB4	I/O	FT	-	SPI1_MISO, EVENTOUT, TIM22_CH1	COMP2_INP		
-	-	-	26	28	28	41	PB5 I/O FT - SPI1_MOSI, LPTIM1_IN1, I2C1_SMBA, TIM22_CH2		COMP2_INP					
-	А3	25	27	29	29	42	PB6	I/O FTf - USART2_TX, I2C1_SCL, LPTIM1_ETR, TIM21_CH1 CO		COMP2_INP				
-	A4	26	28	30	30	43	PB7	I/O	FTf	-	USART2_RX, I2C1_SDA, LPTIM1_IN2	COMP2_INP, VREF_PVD_IN		

Memory mapping STM32L031x4/6

5 Memory mapping

Figure 10. Memory map



^{1.} Refer to the STM32L031x4/6 reference manual for details on the Flash memory organization for each memory size.

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25$ °C and $T_A = T_A$ max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3 σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.6 V (for the 1.65 V \leq V $_{DD}$ \leq 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in Figure 11.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 12*.

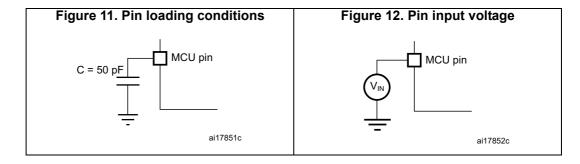


Table 28. Current consumption in Sleep mode

Symbol	Parameter	Cond	litions	f _{HCLK}	Тур	Max ⁽¹⁾	Unit
			Range 3,	1 MHz	36.5	87	
			V _{CORE} =1.2 V,	2 MHz	58	100	
			VOS[1:0]=11	4 MHz	100	170	
		f _{HSE} = f _{HCLK} up to 16 MHz included,	Range 2,	4 MHz	125	190	
		$f_{HSE} = f_{HCLK}/2$	V _{CORE} =1.5 V,	8 MHz	230	310	
		above 16 MHz (PLL ON) ⁽²⁾	VOS[1:0]=10	16 MHz	450	540	
		J.,	Range 1,	8 MHz	275	360	
	Supply current		V _{CORE} =1.8 V,	16 MHz	555	650	
	in Sleep mode, Flash		VOS[1:0]=01	32 MHz	1350	1600	
	memory OFF	HSI16 clock source	Range 2, V _{CORE} =1.5 V, VOS[1:0]=10	16 MHz	585	690	
		(16 MHz)	Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	32 MHz	1500	1700	
		MSI clock	Range 3, V _{CORE} =1.2 V, VOS[1:0]=11	65 kHz	17	43	μΑ
				524 kHz	28	55	
(Cloop)				4.2 MHz	115	190	
I _{DD} (Sleep)		$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$	Range 3, V _{CORE} =1.2 V, VOS[1:0]=11	1 MHz	49	160	
				2 MHz	69	190	
				4 MHz	115	230	
			Range 2, CORE=1.5 V,	4 MHz	135	200	
				8 MHz	240	320	
		above 16 MHz (PLL ON) ⁽²⁾	VOS[1:0]=10	16 MHz	460	550	
			Range 1,	8 MHz	290	370	
	Supply current in Sleep		V _{CORE} =1.8 V,	16 MHz	565	670	
	mode, Flash		VOS[1:0]=01	32 MHz	1350	1600	
	memory ON	HSI16 clock source	Range 2, V _{CORE} =1.5 V, VOS[1:0]=10	16 MHz	600	700	
		(16 MHz)	Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	32 MHz	1500	1700	
			Range 3,	65 kHz	28	55	
		MSI clock	V _{CORE} =1.2 V,	524 kHz	39.5	67	
			VOS[1:0]=11	4.2 MHz	125	200	

^{1.} Guaranteed by characterization results at 125 $^{\circ}\text{C},$ unless otherwise specified.

^{2.} Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Electrical characteristics STM32L031x4/6

Symbol	Parameter	Conditions	Тур	Max ⁽¹⁾	Unit				
I _{DD} (Stop)		$T_A = -40$ °C to 25°C	0.38	0.99					
	Supply current in Stop mode	T _A = 55°C	0.54	1.9					
		T _A = 85°C	1.35	4.2	μΑ				
		T _A = 105°C	3.1	9					
		T _A = 125°C	7.55	19					

^{1.} Guaranteed by characterization results at 125 $^{\circ}\text{C},$ unless otherwise specified.

Figure 18. I_{DD} vs V_{DD} , at T_A = 25/55/ 85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive

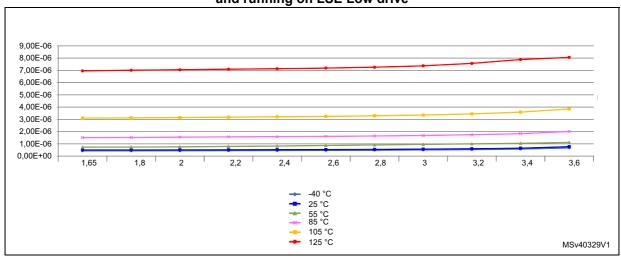
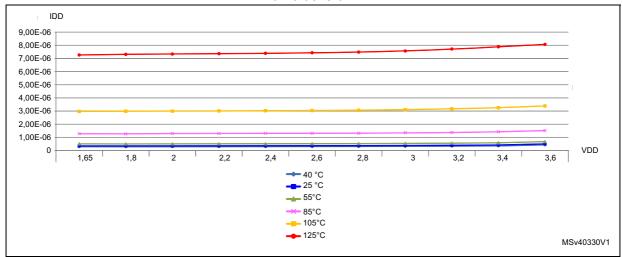


Figure 19. I_{DD} vs V_{DD} , at T_A = 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks off



Typical consumption, $T_A = 25$ °C **Symbol Peripheral** Unit V_{DD}=1.8 V V_{DD}=3.0 V 0.7 1.2 I_{DD(PVD / BOR)} 1.3 1.4 I_{REFINT} LSE Low drive⁽²⁾ 0.1 0.1 LSI 0.27 0.31 **IWDG** 0.2 0.3 LPTIM1, Input 100 Hz 0.01 0.01 μΑ LPTIM1, Input 1 MHz 6 6 LPUART1 0.2 0.2 RTC (LSE in Bypass 0.2 0.2 mode)

Table 35. Peripheral current consumption in Stop and Standby mode⁽¹⁾

6.3.5 Wakeup time from low-power mode

The wakeup times given in the following table are measured with the MSI or HSI16 RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is either the MSI oscillator in the range configured before entering Stop mode, the HSI16 or HSI16/4.
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*.

^{1.} LPTIM, LPUART peripherals can operate in Stop mode but not in Standby mode

^{2.} LSE Low drive consumption is the difference between an external clock on OSC32_IN and a quartz between OSC32_IN and OSC32_OUT.-

Condition Unit **Symbol Parameter** Тур Max MSI range 0 30 MSI range 1 20 MSI range 2 15 MSI range 3 10 MSI range 4 6 μs MSI oscillator startup time t_{SU(MSI)} MSI range 5 5 MSI range 6, Voltage range 1 3.5 and 2 MSI range 6, 5 Voltage range 3 MSI range 0 40 MSI range 1 20 MSI range 2 10 MSI range 3 4 MSI range 4 2.5 $t_{STAB(MSI)}^{(2)}$ MSI oscillator stabilization time μs MSI range 5 2 MSI range 6, Voltage range 1 2 and 2 MSI range 3, 3 Voltage range 3 Any range to 4 range 5 MHz MSI oscillator frequency overshoot f_{OVER(MSI)}

Table 43. MSI oscillator characteristics (continued)

6.3.8 **PLL** characteristics

The parameters given in *Table 44* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*.

Table 44. PLL characteristics

Any range to

range 6

Symbol	Parameter		Unit			
Symbol	Faranteter	Min	Тур	Max ⁽¹⁾	Oilit	
f _{PLL_IN}	PLL input clock ⁽²⁾	2	-	24	MHz	
	PLL input clock duty cycle	45	-	55	%	



6

^{1.} This is a deviation for an individual part, once the initial frequency has been measured.

^{2.} Guaranteed by characterization results.

Electrical characteristics STM32L031x4/6

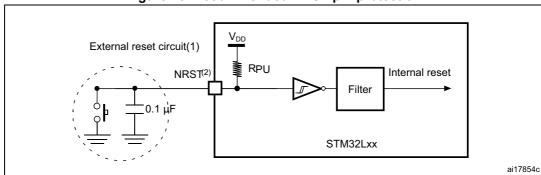


Figure 28. Recommended NRST pin protection

- 1. The reset network protects the device against parasitic resets.
- 2. The user must ensure that the level on the NRST pin can go below the V_{IL(NRST)} max level specified in *Table 56*. Otherwise the reset will not be taken into account by the device.

6.3.15 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 57* are values derived from tests performed under ambient temperature, f_{PCLK} frequency and V_{DDA} supply voltage conditions summarized in *Table 20: General operating conditions*.

Note: It is recommended to perform a calibration after each power-up.

Table 57. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
\/	Analog supply voltage for	Fast channel	1.65	-	3.6	- V	
V_{DDA}	ADC on	Standard channel	1.75 ⁽¹⁾	-	3.6		
	Current consumption of the	1.14 Msps	-	200	-		
	ADC on V _{DDA}	10 ksps	-	40	-		
I _{DDA} (ADC)	Current consumption of the	1.14 Msps	-	70	-	μA	
	ADC on V _{DD} ⁽²⁾	10 ksps	-	1	-		
		Voltage scaling Range 1	0.14	-	- 16		
f _{ADC}	ADC clock frequency	Voltage scaling Range 2	0.14	-	8	MHz	
		Voltage scaling Range 3	0.14	-	4		
f _S ⁽³⁾	Sampling rate		0.05	-	1.14	MHz	
£ (3)	External trigger frequency	f _{ADC} = 16 MHz	-	-	941	kHz	
f _{TRIG} ⁽³⁾	External trigger frequency		-	-	17	1/f _{ADC}	
V _{AIN}	Conversion voltage range		0	-	V_{DDA}	V	
R _{AIN} ⁽³⁾	External input impedance	See Equation 1 and Table 58 for details	-	-	50	kΩ	
R _{ADC} ⁽³⁾⁽⁴⁾	Sampling switch resistance		-	-	1	kΩ	
C _{ADC} ⁽³⁾	Internal sample and hold capacitor		-	-	8	pF	

Electrical characteristics STM32L031x4/6

Table 58.	R _{AIN} m	ax for fand	_C = 16 MHz ⁽¹⁾
	···AIN ····	~^ . ~ ADC	,

T _s (cycles)	t _S (µs)	R _{AIN} max for fast channels (kΩ)	R _{AIN} max for standard channels (kΩ)						
			V _{DD} > 2.7 V	V _{DD} > 2.4 V	V _{DD} > 2.0 V	V _{DD} > 1.8 V	V _{DD} > 1.75 V	V _{DD} > 1.65 V and T _A > -10 °C	V _{DD} > 1.65 V and T _A > 25 °C
1.5	0.09	0.5	< 0.1	NA	NA	NA	NA	NA	NA
3.5	0.22	1	0.2	< 0.1	NA	NA	NA	NA	NA
7.5	0.47	2.5	1.7	1.5	< 0.1	NA	NA	NA	NA
12.5	0.78	4	3.2	3	1	NA	NA	NA	NA
19.5	1.22	6.5	5.7	5.5	3.5	NA	NA	NA	< 0.1
39.5	2.47	13	12.2	12	10	NA	NA	NA	5
79.5	4.97	27	26.2	26	24	< 0.1	NA	NA	19
160.5	10.03	50	49.2	49	47	32	< 0.1	< 0.1	42

^{1.} Guaranteed by design.

Table 59. ADC accuracy⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ET	Total unadjusted error		-	2	4	
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	LSB
EL	Integral linearity error		-	1.5	2.5	
ED	Differential linearity error		-	1	1.5	
	Effective number of bits	1.65 V < V _{DDA} < 3.6 V, range	10.2	11		
ENOB	Effective number of bits (16-bit mode oversampling with ratio =256) ⁽⁴⁾	1/2/3	11.3	12.1	-	bits
SINAD	Signal-to-noise distortion		63	69	-	
	Signal-to-noise ratio		63	69	-	
SNR	Signal-to-noise ratio (16-bit mode oversampling with ratio =256) ⁽⁴⁾		70	76	-	dB
THD	Total harmonic distortion		-	-85	-73	

^{1.} ADC DC accuracy values are measured after internal calibration.

- 3. Better performance may be achieved in restricted V_{DDA} , frequency and temperature ranges.
- 4. This number is obtained by the test board without additional noise, resulting in non-optimized value for oversampling mode.

DocID027063 Rev 4 86/118

^{2.} ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input ADC Accuracy vs. Negative injection current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.

Any positive injection current within the limits specified for I_{INJ(PIN)} and ΣI_{INJ(PIN)} in Section 6.3.12 does not affect the ADC accuracy.

Table 68. SPI characteristics in voltage Range 2 (1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode			8	
f _{SCK} 1/t _{c(SCK)}	SPI clock frequency	Slave mode Transmitter 1.65 <v<sub>DD<3.6V</v<sub>	-	-	8	MHz
····C(SCK)		Slave mode Transmitter 2.7 <v<sub>DD<3.6V</v<sub>			8 ⁽²⁾	
Duty _(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
t _{su(NSS)}	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	
t _{h(NSS)}	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
t _{w(SCKH)}	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
t _{su(MI)}	Data input actual times	Master mode	12	-	-	
t _{su(SI)}	Data input setup time	Slave mode	11	-	-	
t _{h(MI)}	Data input hold time	Master mode	6.5	-	-	
t _{h(SI)}	Data input noid time	Slave mode	2	-	-	ns
t _{a(SO}	Data output access time	Slave mode	18	-	52	
t _{dis(SO)}	Data output disable time	Slave mode	12	-	42	
t _{v(SO)}	Data output valid time	Slave mode	-	40	55	
, ,		Master mode	-	16	26	
t _{v(MO)}	Data output hold times	Slave mode	12	-	-]
t _{h(SO)}	Data output hold time	Master mode	4	-	-	

^{1.} Guaranteed by characterization results.

^{2.} The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while $Duty_{(SCK)} = 50\%$.

Package information STM32L031x4/6

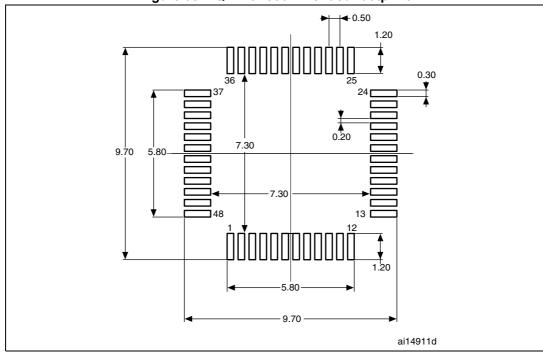


Figure 35. LQFP48 recommended footprint

1. Dimensions are expressed in millimeters.

LQFP48 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

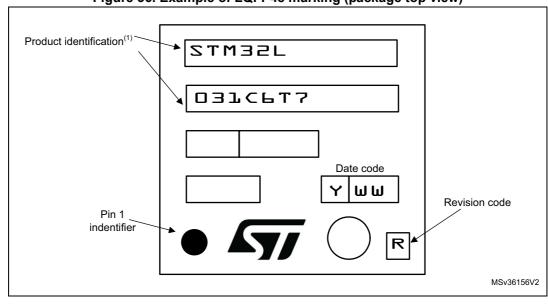


Figure 36. Example of LQFP48 marking (package top view)

5//

^{1.} Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.2 LQFP32 package information

SEATING PLANE С 0.25 mm GAUGE PLANE С CCC D F D1 D3 16 \blacksquare ⊞ --₩ Ш -------____9 PIN 1 **IDENTIFICATION** 5V_ME_V2

Figure 37. LQFP32, 7 x 7 mm, 32-pin low-profile quad flat package outline

1. Drawing is not to scale.

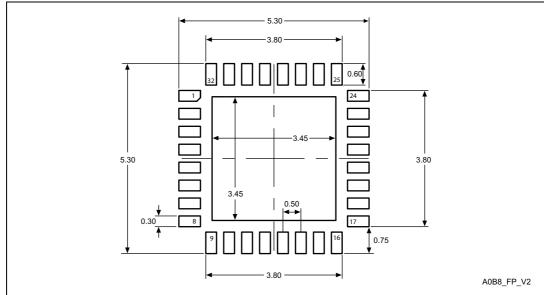


Figure 41. UFQFPN32 recommended footprint

1. Dimensions are expressed in millimeters.

UFQFPN32 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

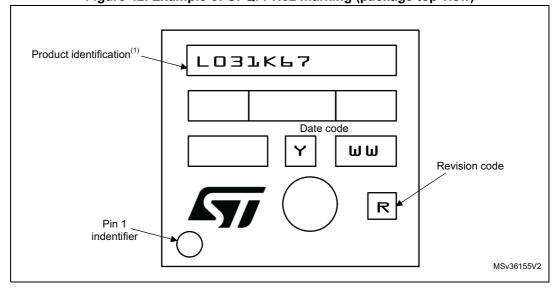


Figure 42. Example of UFQFPN32 marking (package top view)

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

TSSOP20 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

Product identification⁽¹⁾

Pin 1

indentifier

Date code Revision code

Y WW R

MSv37838V1

Figure 51. Example of TSSOP20 marking (package top view)

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

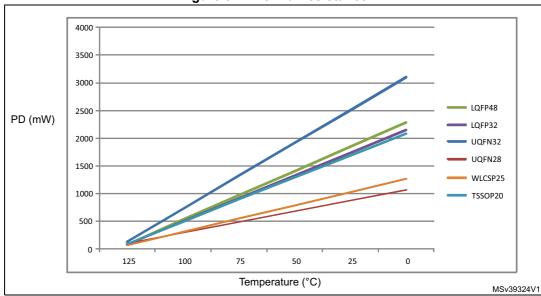


Figure 52. Thermal resistance

1. The above curves are valid for range 6. For range 7, the curves are shifted by 20 °C to the right.

7.7.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

STM32L031x4/6 Revision history

9 Revision history

Table 79. Document revision history

18-Sep-2015 Initial release. Datasheet status changed to production data. Updated power consumption in run mode on cover page. Updated Table 5: Functionalities depending on the working mode (from Run/active down to standby). Modified Figure 6: STM32L031x4/6 UFQFPN28 pinout and Table 15: Pin definitions. Updated power dissipation (P _D) in Table 20: General operating conditions. Updated current consumption with all peripherals enabled in Table 34: Peripheral current consumption in Run or Sleep mode and Table 35: Peripheral current consumption in Stop and Standby mode. Modified t _{WSTOP} for f _{HCLK} =65 MHz in Table 36: Low-power mode wakeup timings. Updated Table 24: Current consumption in Run mode, code with data processing running from Flash memory, Table 25: Current consumption in Run mode vs code type, code with data processing running from Flash memory, Figure 15: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE = 16 MHz, 1WS and Figure 16: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE = 16 MHz, 1WS and Figure 16: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSI16, 1WS. Updated Table 26: Current consumption in Run mode, code with data processing running from RAM and Table 27: Current consumption in Run mode vs code type, code with data processing running from RAM, Table 28: Current consumption in Sleep mode. Updated Table 29: Current consumption in Low-power run mode and Figure 17: IDD vs VDD, at TA= 25/55/85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS. Updated Table 30: Current consumption in Low-power Sleep mode. Updated Table 31: Typical and maximum current consumption in Stop mode, Table 32: Typical and maximum current Consumption in Stop mode, Table 32: Typical and maximum current consumption in Stop mode.
consumption in run mode on cover page. Updated Table 5: Functionalities depending on the working mode (from Run/active down to standby). Modified Figure 6: STM32L031x4/6 UFQFPN28 pinout and Table 15: Pin definitions. Updated power dissipation (PD) in Table 20: General operating conditions. Updated current consumption with all peripherals enabled in Table 34: Peripheral current consumption in Run or Sleep mode and Table 35: Peripheral current consumption in Stop and Standby mode. Modified twsTop for fHCLK=65 MHz in Table 36: Low-power mode wakeup timings. Updated Table 24: Current consumption in Run mode, code with data processing running from Flash memory, Table 25: Current consumption in Run mode vs code type, code with data processing running from Flash memory, Figure 15: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSIE = 16 MHz, 1WS and Figure 16: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSI6, 1WS. Updated Table 26: Current consumption in Run mode, code with data processing running from RAM and Table 27: Current consumption in Run mode vs code type, code with data processing running from RAM, Table 28: Current consumption in Sleep mode. Updated Table 29: Current consumption in Low-power run mode and Figure 17: IDD vs VDD, at TA= 25/55/85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS. Updated Table 30: Current consumption in Low-power Sleep mode. Updated Table 31: Typical and maximum current consumptions in Stop mode, Table 32: Typical and maximum current consumptions in Stop mode, Table 32: Typical and maximum current consumptions in Stop mode, Table 32: Typical and maximum current
consumptions in Standby mode, Figure 18: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive and Figure 19: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks off.
25/55/ 85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive and Figure 19: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks

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47/